P-Channel 1.2-V (G-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ)
- 8	0.035 at V_{GS} = - 4.5 V	- 11.7	21 nC
	0.042 at V_{GS} = - 2.5 V	- 10.7	
	0.052 at V_{GS} = - 1.8 V	- 9.6	
	0.069 at V_{GS} = - 1.5 V	- 8.3	
	0.098 at V_{GS} = - 1.2 V	- 1.02	

FEATURES

- TrenchFET® Power MOSFET
- Industry First 1.2 V Rated MOSFET
- Ultra Small MICRO FOOT® Chipscale Packaging Reduces Footprint Area, Profile (0.62 mm) and On-Resistance Per Footprint Area

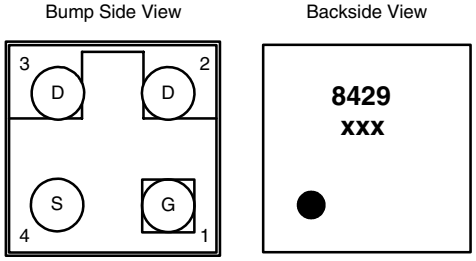
Pb-free

RoHS COMPLIANT

APPLICATIONS

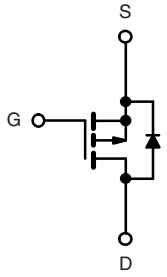
- Low Threshold Load Switch for Portable Devices
  - Low Power Consumption
  - Increased Battery Life
- Ultra Low Voltage Load Switch

MICRO FOOT



Device Marking: 8429
xxx = Date/Lot Traceability Code

Ordering Information: Si8429DB-T1-E1 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 8	V
Gate-Source Voltage		V_{GS}	± 5	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 11.7	A
	T_C = 70 °C		- 9.4	
	T_A = 25 °C		- 7.8[b, c]	
	T_A = 70 °C		- 6.3[b, c]	
Pulsed Drain Current		I_{DM}	- 25	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 5.7	
	T_A = 25 °C		- 2.5[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	6.25	W
	T_C = 70 °C		4	
	T_A = 25 °C		2.77[b, c]	
	T_A = 70 °C		1.77[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Package Reflow Conditions[d]	VPR		260	
	IR/Convection		260	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 Board.
c. t = 10 s.
d. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.
e. In this document, any reference to the *Case* represents the body of the MICRO FOOT device and *Foot* is the bump.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a, b]		R_{thJA}	35	45	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	20	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.
b. Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 7.5		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 2.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.35		- 0.8	V
		V_{DS} = V_{GS}, I_D = - 5 mA		- 0.6		
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 8 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 8 V, V_{GS} = 0 V, T_J = 70 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ 5 V, V_{GS} = - 4.5 V	- 5			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 1 A		0.029	0.035	Ω
		V_{GS} = - 2.5 V, I_D = - 1 A		0.035	0.042	
		V_{GS} = - 1.8 V, I_D = - 1 A		0.043	0.052	
		V_{GS} = - 1.5 V, I_D = - 1 A		0.051	0.069	
		V_{GS} = - 1.2 V, I_D = - 1 A		0.065	0.098	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 4 V, I_D = - 1 A		0.7	1.2	S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 4 V, V_{GS} = 0 V, f = 1 MHz		1640		pF
Output Capacitance	C_{oss}			590		
Reverse Transfer Capacitance	C_{rss}			380		
Total Gate Charge	Q_g	V_{DS} = - 4 V, V_{GS} = - 5 V, I_D = - 1 A		24	26	nC
		V_{DS} = - 4 V, V_{GS} = - 4.5 V, I_D = 1 A		21	32	
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			3.7		
Gate Resistance	R_g	V_{GS} = - 0.1 V, f = 1 MHz		22		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 4 V, R_L = 4 Ω $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		12	20	ns
Rise Time	t_r			25	40	
Turn-Off Delay Time	$t_{d(off)}$			260	390	
Fall Time	t_f			155	240	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 2.5	A
Pulse Diode Forward Current	I_{SM}				- 25	
Body Diode Voltage	V_{SD}	I_S = - 1 A, V_{GS} = 0 V		- 0.7	- 1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 1 A, di/dt = 100 A/µs, T_J = 25 °C		150	250	ns
Body Diode Reverse Recovery Charge	Q_{rr}			150	230	nC
Reverse Recovery Fall Time	t_a			57		ns
Reverse Recovery Rise Time	t_b			93		

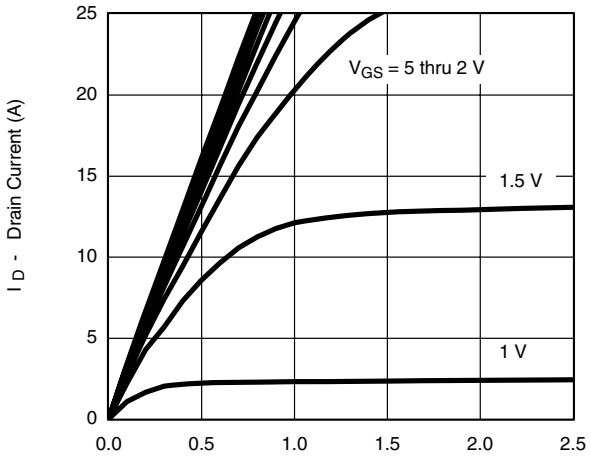
Notes:

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

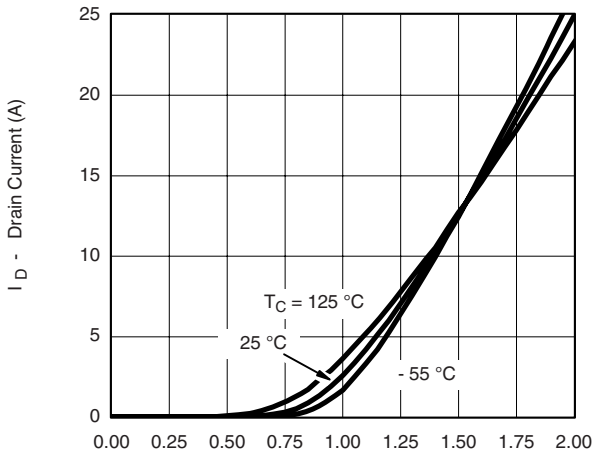
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

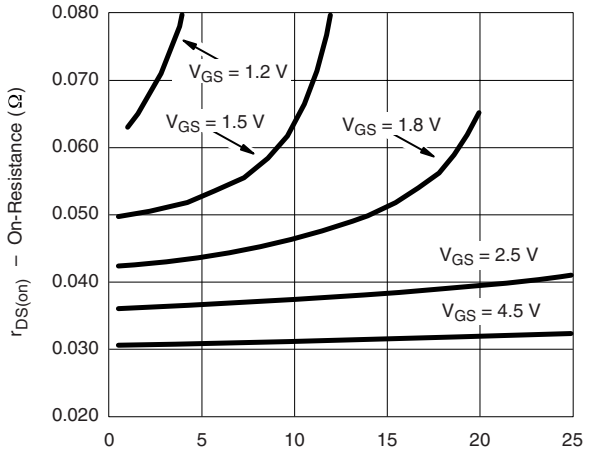
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



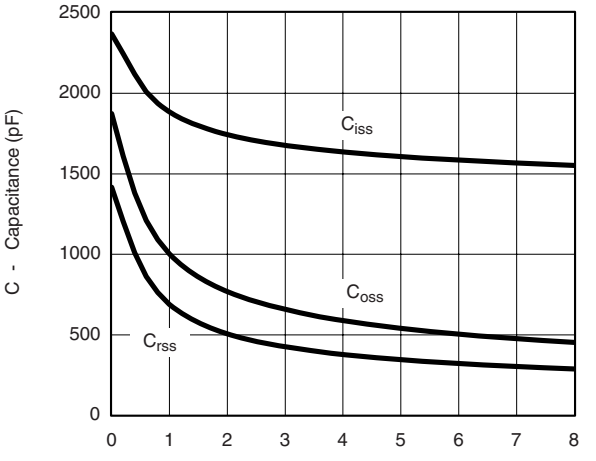
Output Characteristics



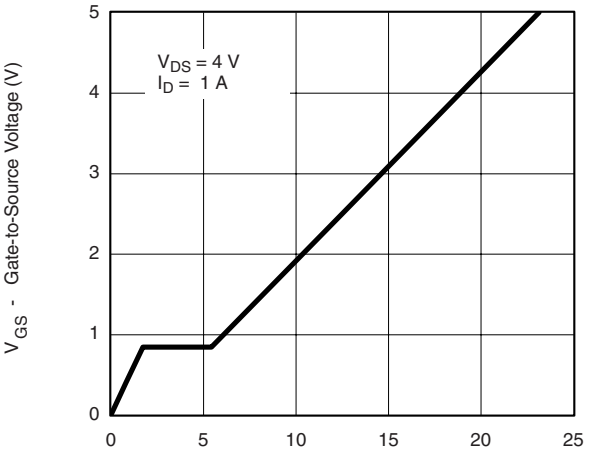
Transfer Characteristics



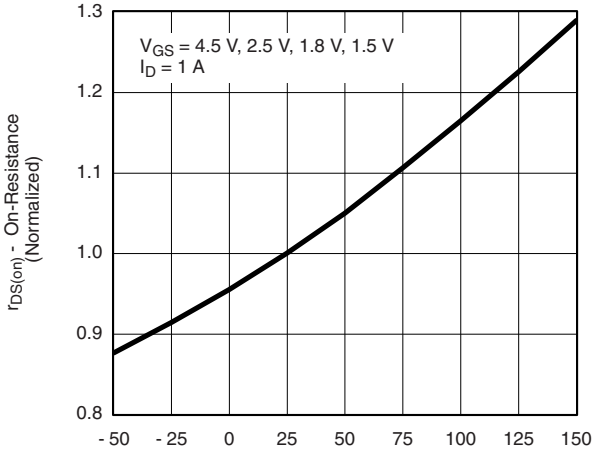
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

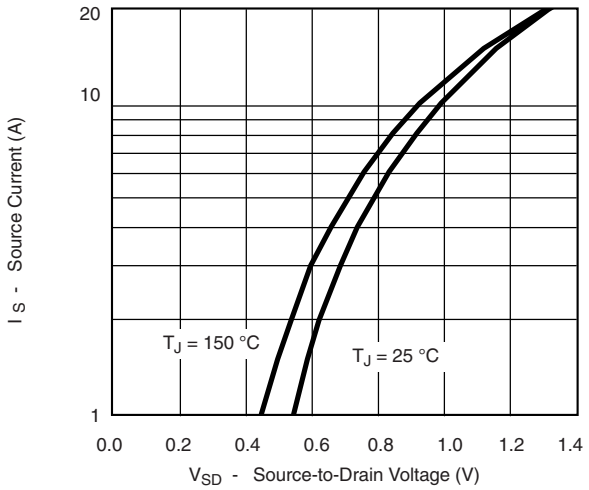


Gate Charge

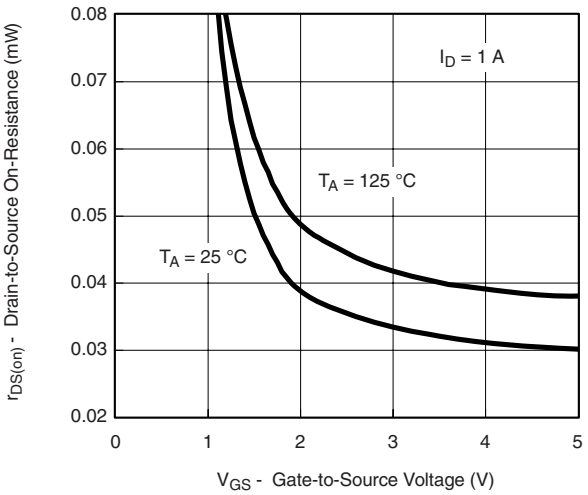


On-Resistance vs. Junction Temperature

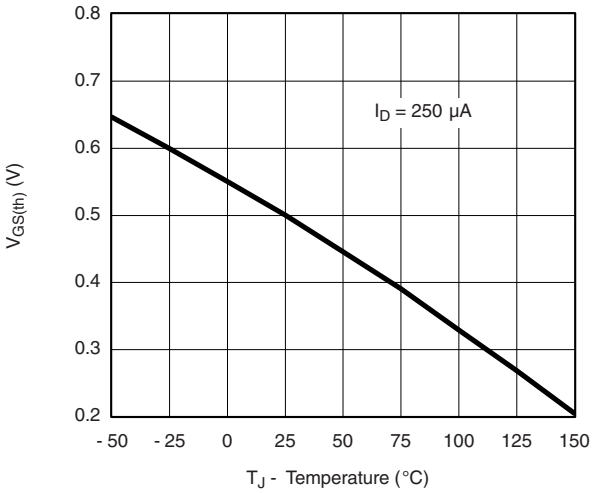
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



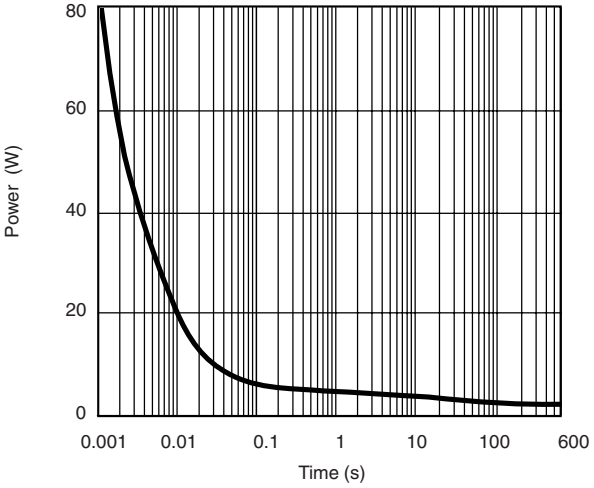
Source-Drain Diode Forward Voltage



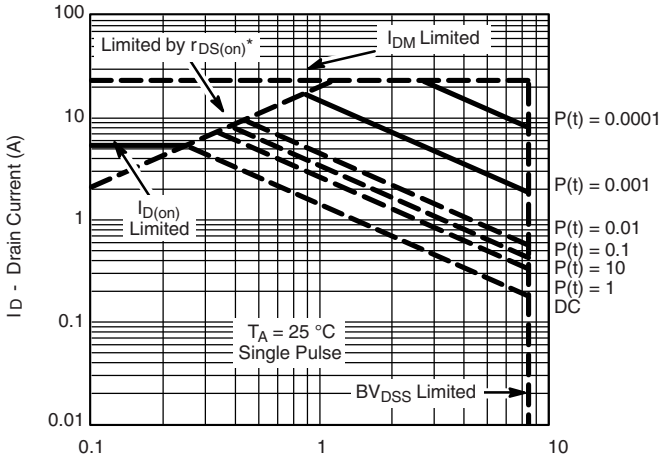
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



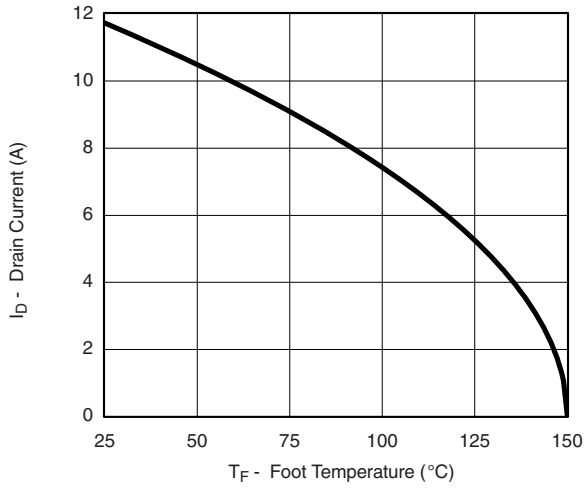
Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

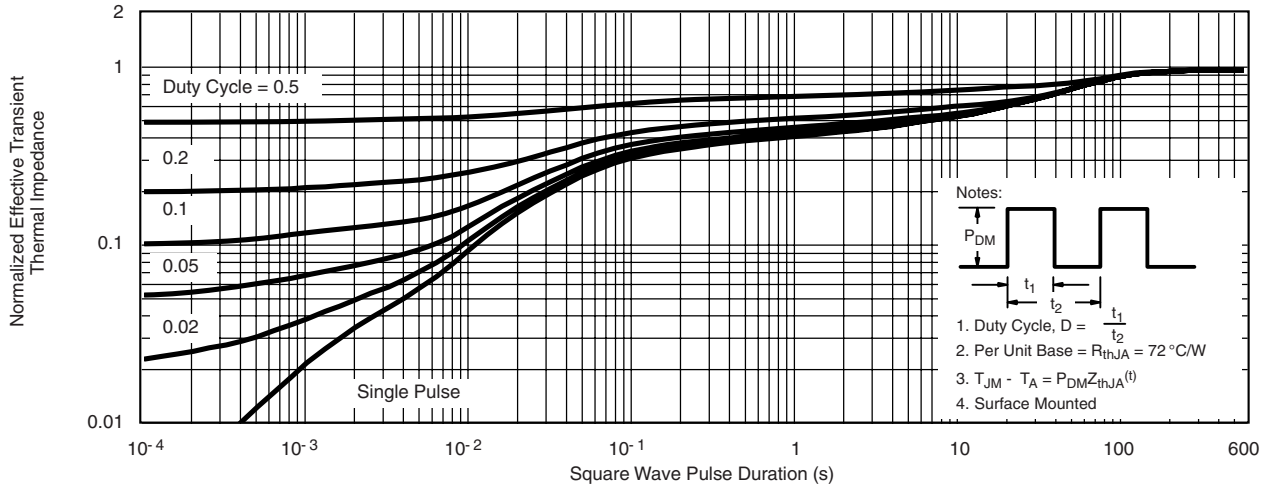
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

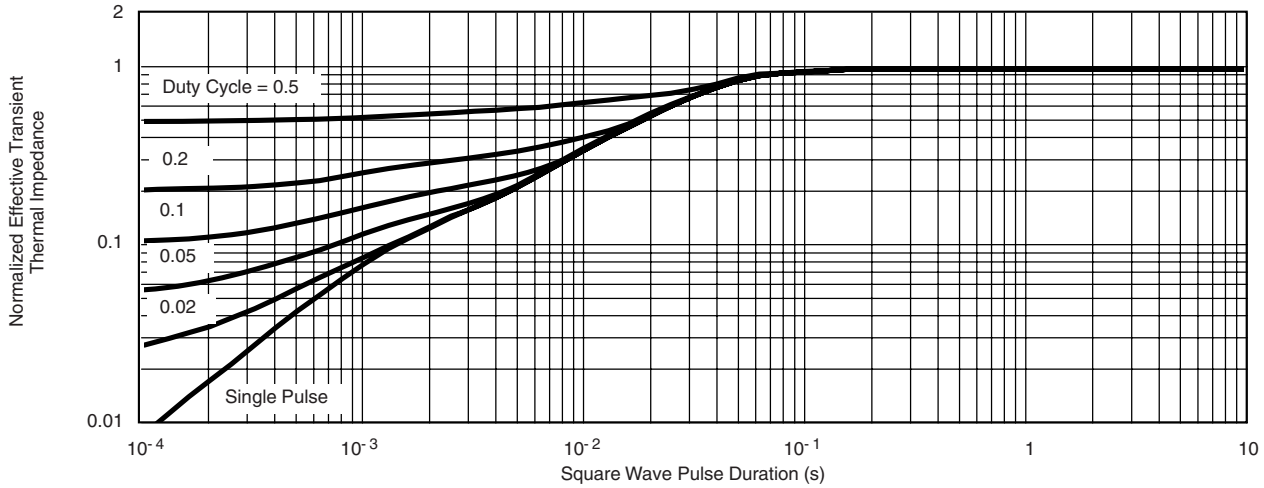


Current Derating*

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



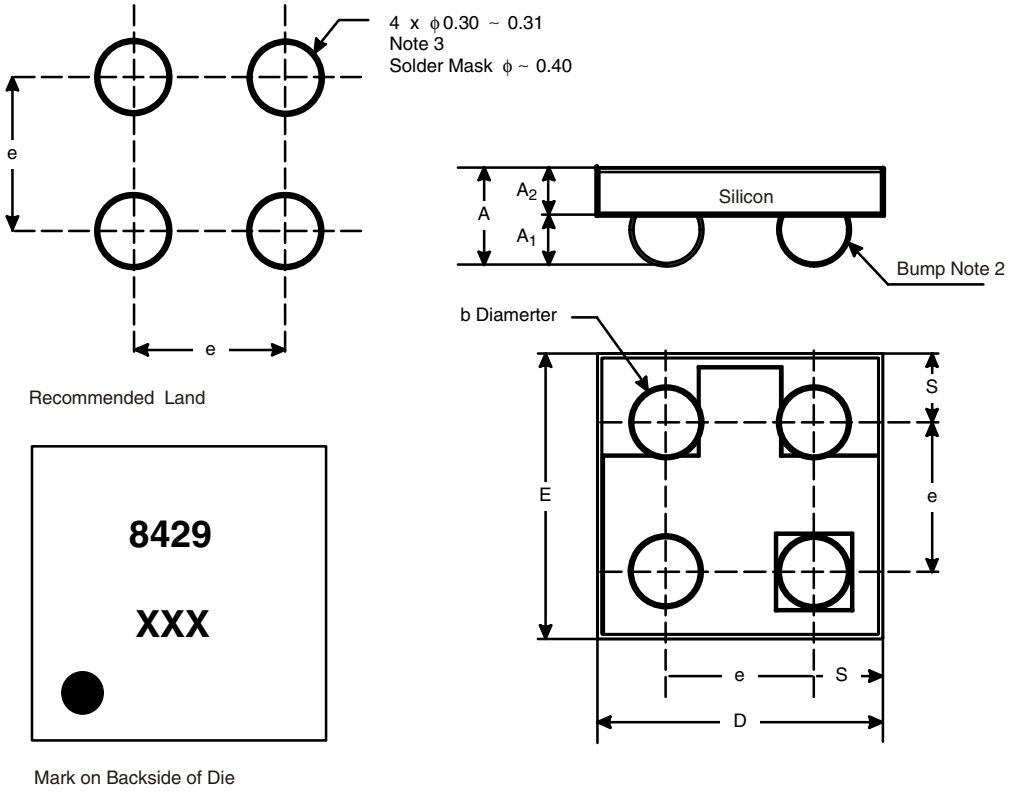
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

PACKAGE OUTLINE

MICRO FOOT: 4-BUMP (2 x 2, 0.8 mm PITCH)



Notes (Unless Otherwise Specified):
1. Laser mark on the silicon die back, coated with a thin metal.
2. Bumps are Sn/Ag/Cu.
3. Non-solder mask defined copper landing pad.
4. The flat side of wafers is oriented at the bottom.

Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	0.600	0.650	0.0236	0.0256
A_1	0.260	0.290	0.0102	0.0114
A_2	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.520	1.600	0.0598	0.0630
E	1.520	1.600	0.0598	0.0630
e	0.750	0.850	0.0295	0.0335
S	0.370	0.380	0.0146	0.0150

* Use millimeters as the primary measurement

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74399.

Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.